

Device Modeling Report

COMPONENTS:

DIODE/ GENERAL PURPOSE RECTIFIER / PROFESSIONAL

PART NUMBER: RURG5060

MANUFACTURER: INTERSIL

REMRAK: TC=110C

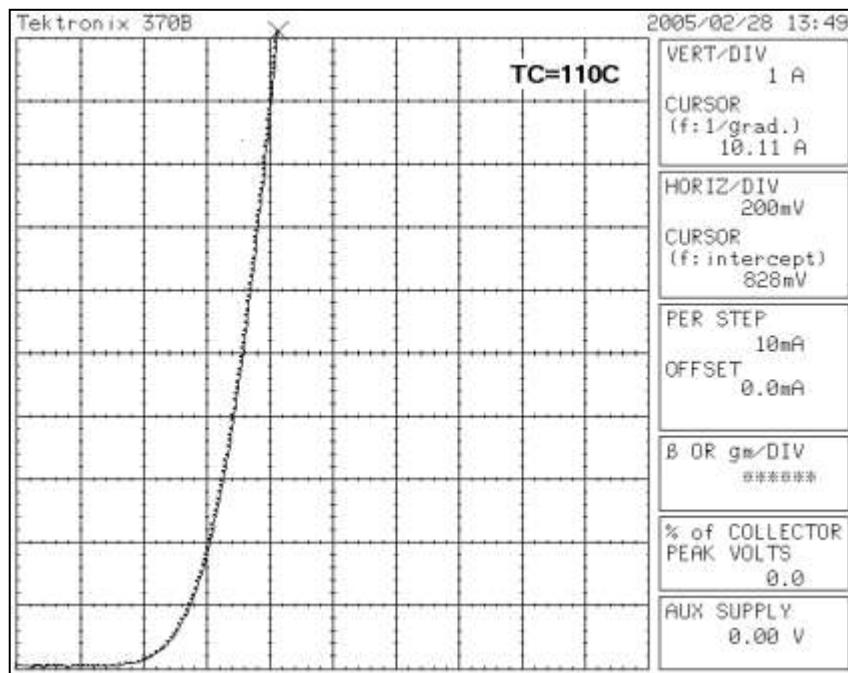


Bee Technologies Inc.

PSpice model parameter	Model description
S	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

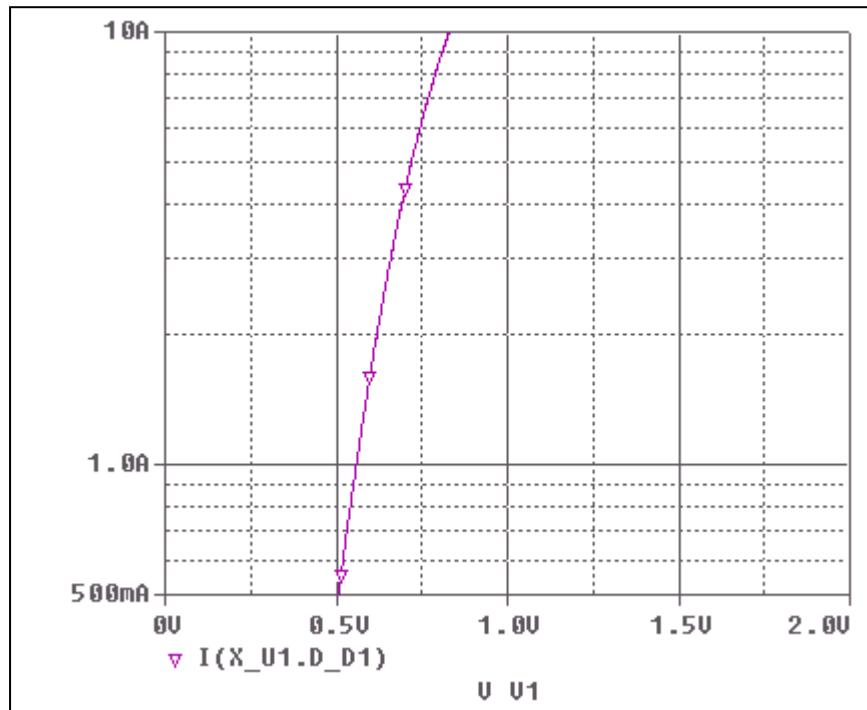
Forward Current Characteristic

Reference

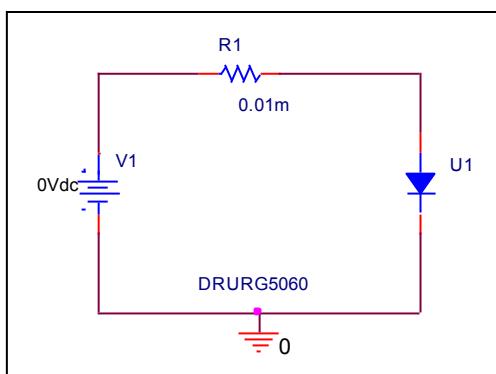


Forward Current Characteristic

Circuit Simulation Result

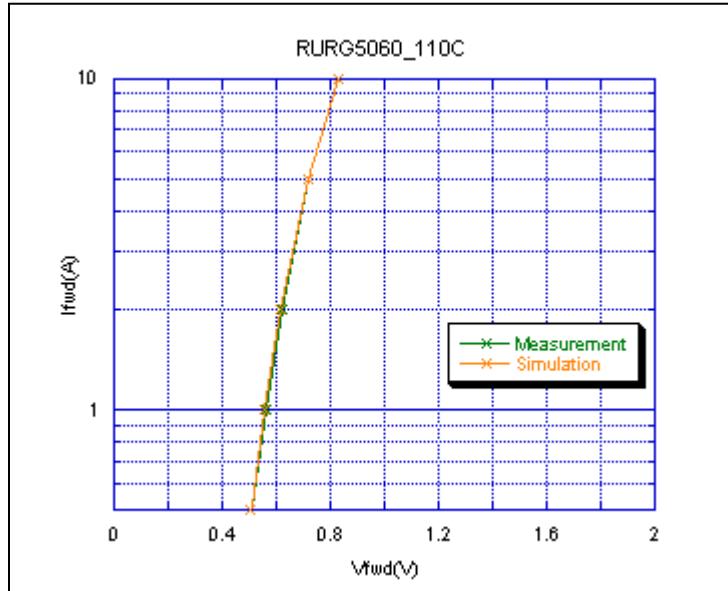


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

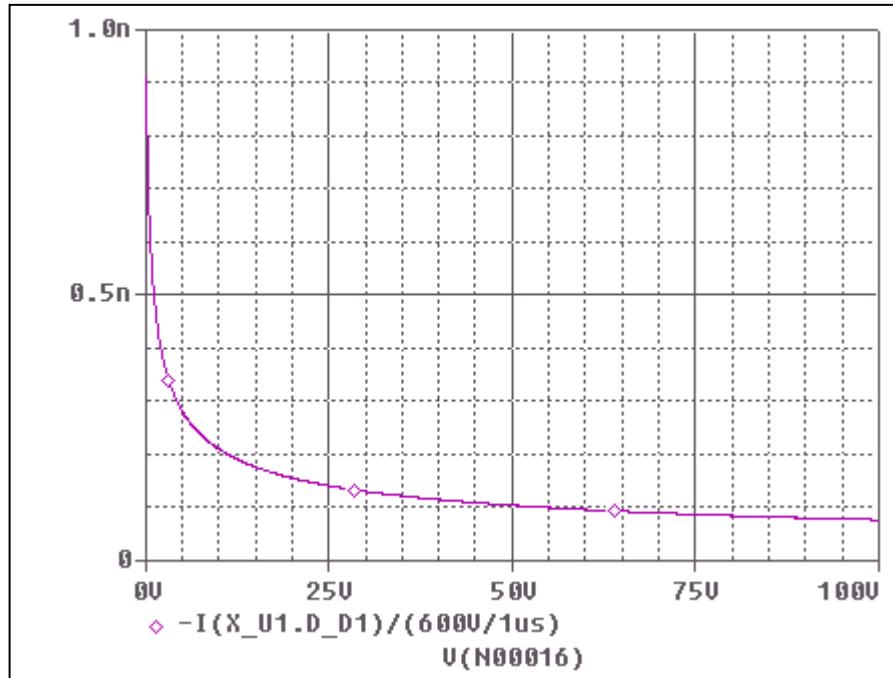


Simulation Result

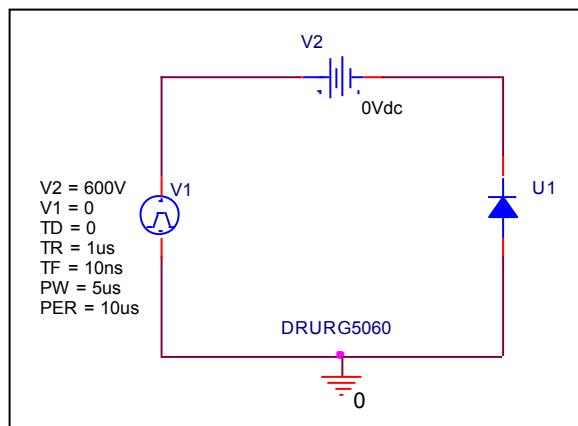
$I_{fwd}(A)$	$V_{fwd}(V)$ Measurement	$V_{fwd}(V)$ Simulation	%Error
0.5	0.500	0.505	-1.00
1	0.560	0.558	0.36
2	0.622	0.618	0.64
5	0.721	0.719	0.28
10	0.828	0.829	-0.12

Capacitance Characteristic

Circuit Simulation Result

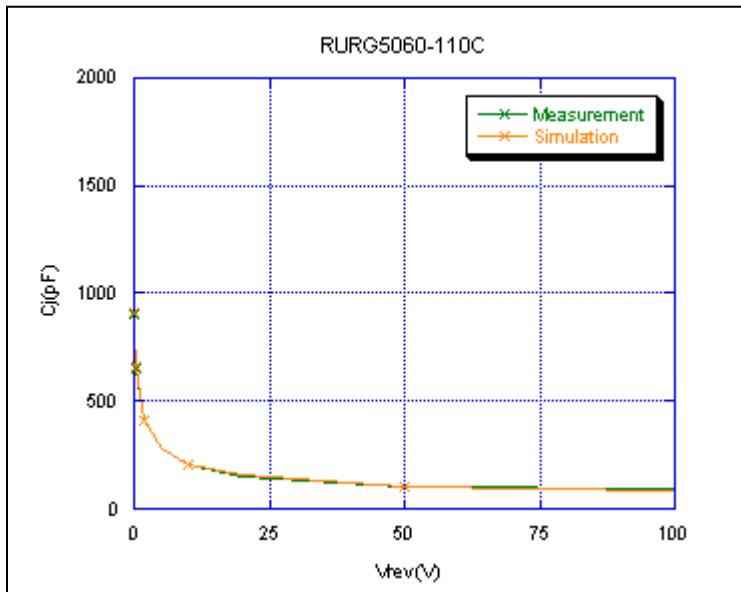


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

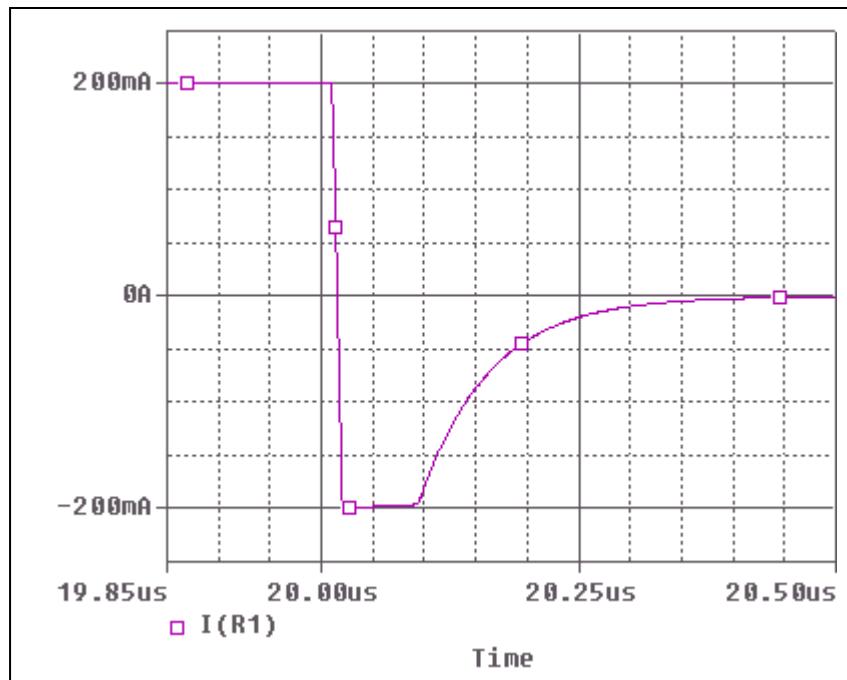


Simulation Result

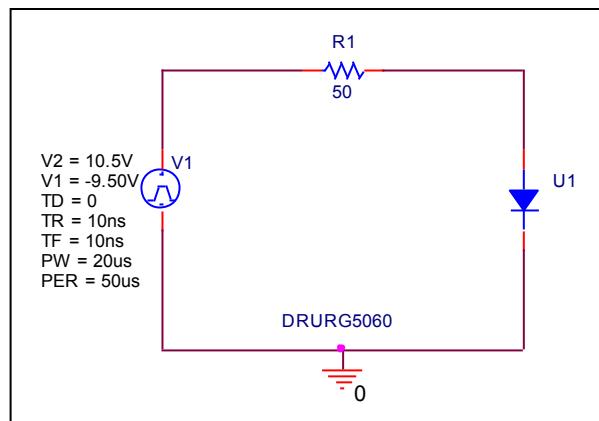
V_{rev} (V)	C_j (pF) Measurement	C_j (pF) Simulation	%Error
0	1015.300	1015.300	0.00
0.1	899.359	910.925	-1.29
0.2	818.092	818.088	0.00
0.5	650.305	658.357	-1.24
1	520.625	528.628	-1.54
2	410.957	409.216	0.42
5	281.052	282.702	-0.59
10	210.485	210.728	-0.12
20	150.863	156.107	-3.48
50	108.678	104.377	3.96

Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit

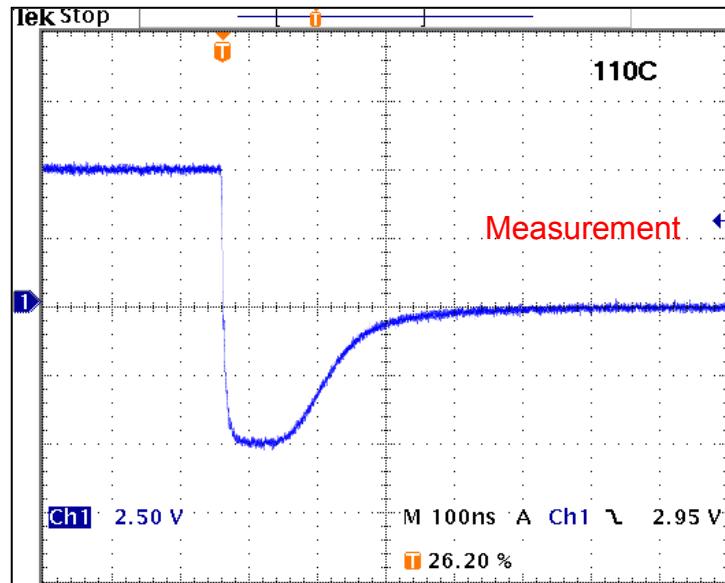


Compare Measurement vs. Simulation

	Measurement		Simulation		%Error
trj	78.0	ns	77.9	ns	0.128
trb	156.0	ns	155.7	ns	0.192

Reverse Recovery Characteristic

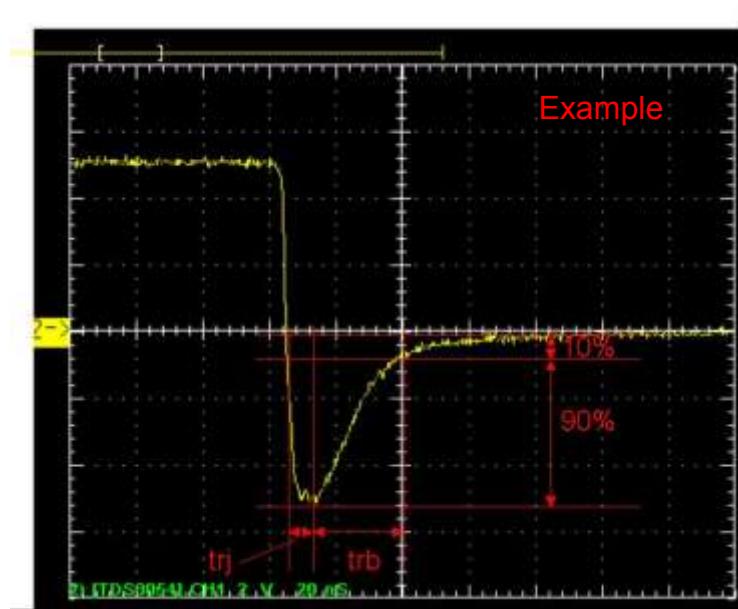
Reference



Trj = 78 (ns)

Trb=156 (ns)

Conditions: Ifwd=Irev=0.2(A), RI=50



Relation between trj and trb